

What is claimed is:

1. A method comprising:

introducing a dielectric layer over a substrate between an interconnection line and a contact point on the substrate, the dielectric layer comprising a plurality of different material layers; and

patterning an interconnection to the contact point.

- 2. The method of claim 1, wherein patterning an interconnection to the contact point comprises patterning an interconnection directly to a device on the substrate.
- 3. The method of claim 2, wherein introducing the dielectric layer comprises introducing a plurality of alternating material layers.
- 4. The method of claim 3, wherein the introducing the dielectric layer comprises introducing silicon dioxide as the ultimate layer.
- 5. The method of claim 4, wherein introducing a plurality of alternating material layers comprises alternating silicon dioxide layers with at least one other material layers.
- 6. The method of claim 5, wherein the number of alternating silicon dioxide layers comprises at least six.

7. The method of claim 1, wherein the dielectric layer comprises a first dielectric layer, the method further

Sub Q' comprising introducing a second dielectric layer between the first dielectric layer and the etch stop layer.

8. A method comprising:

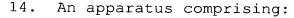
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introducing a dielectric layer over a substrate between an interconnection line and the substrate, the dielectric layer comprising a plurality of alternating material layers; and

patterning an interconnection to the substrate.

- 9. The method of claim 8, wherein the interconnection line comprises a first level interconnection line.
- 10. The method of claim 9, wherein introducing a plurality of alternating material layers comprises introducing silicon dioxide as the ultimate material layer.
- 11. The method of claim 10, wherein introducing a plurality of alternating material layers comprises alternating silicon dioxide layers with at least one other material layers.
- 12. The method of claim 11, wherein the number of alternating silicon dioxide layers comprises at least six.
- 13. The method of claim 8, wherein the dielectric layer comprises a first dielectric layer, the method further comprising introducing a second dielectric layer between the first dielectric layer and the substrate.





a substrate comprising a plurality of devices formed thereon; and

an interlayer dielectric layer comprising a base layer and a cap layer, the cap layer comprising a plurality of alternating material layers overlying the substrate.

- 15. The apparatus of claim 14, wherein the cap layer comprises silicon dioxide as the ultimate material layer.
- 16. The apparatus of claim 14, wherein the cap layer comprises a plurality of silicon dioxide layers alternated with at least one other material layers.
- 17. The apparatus of claim 16, wherein the number of alternating silicon dioxide layers comprises at least six.

